Electronic Supplementary Information for:

Low Voltage Electrolyte-Gated Organic Transistors Making Use of High Surface Area Activated Carbon Gate Electrodes

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Fig. S1 Frequency dependence of the capacitance of the MEH-PPV working electrode at 0.8 V vs activated carbon (small sized) quasi reference electrode with activated carbon gate as the counter electrode.
Fig. S2 Transfer characteristics in the saturation regime ($V_{ds} = -0.3$ V) for [EMIM][TFSI]-gated MEH-PPV transistors, sweep rate 50 mV·s$^{-1}$. 
Fig. S3 [EMIM][TFSI]-gated MEH-PPV transistor transfer characteristics in the linear regime ($V_{ds} = -0.1$ V). $I_{ds}$ (left axis, solid black line) and $I_{gs}$ (right axis, dotted blue line) are plotted vs $V_{gs}$, sweep rate 10 mV·s$^{-1}$. 

![Graph showing transistor transfer characteristics](image-url)